

### **Description**

The HXY6005MI uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})}$ , This device is suitable

for use as a load switch or in PWM applications.

G SOT-23-3L

**General Features** 

 $V_{DS} = 60V, I_{D} = 5A$ 

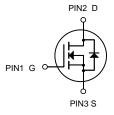
 $R_{DS(ON)}$  < 49m $\Omega$  @  $V_{GS}$ = 10V

### **Application**

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HXY6005MI	SOT-23-3L	6005	3000

### Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V <sub>DS</sub>	Drain-Source Voltage	60	V	
Vgs	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Drain Current-Continuous	5	А	
Ірм	Drain Current-Pulsed (Note 1)	30	А	
P <sub>D</sub>	Maximum Power Dissipation	3	W	
Тл,Тѕтс	Operating Junction and Storage Temperature Range -55 To 150		°C	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	73	°C/W	



# **Electrical Characteristics** (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units	
Off Charac	Off Characteristic						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60	-	-	V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V,	-	-	1.0	μA	
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA	
On Charac	On Characteristics						
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1	1.6	2.5	V	
П	Static Drain-Source on-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =15A	-	40	49	m 0	
R <sub>DS(on)</sub>	note3	V <sub>GS</sub> =4.5V, I <sub>D</sub> =10A	-	45	63	mΩ	
Dynamic C	Dynamic Characteristics						
C <sub>iss</sub>	Input Capacitance		-	825	-	pF	
Coss	Output Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	49	-	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	41	-	pF	
Qg	Total Gate Charge	\/ 00\/ L 45A	-	14	-	nC	
Q <sub>gs</sub>	Gate-Source Charge	$V_{DS}$ =30V, $I_{D}$ =4.5A, $V_{GS}$ =10V	-	2.9	-	nC	
Q <sub>gd</sub>	Gate-Drain("Miller") Charge	VGS-1UV	-	5.2	-	nC	
Switching	Switching Characteristics						
t <sub>d(on)</sub>	Turn-on Delay Time	\/ 00\/\ 01	-	5	-	ns	
t <sub>r</sub>	Turn-on Rise Time	$V_{DS}=30V,I_{D}=2A,$ $R_{I}=6.7\Omega,R_{G}=3\Omega,$	-	2.6	-	ns	
t <sub>d(off)</sub>	Turn-off Delay Time	$V_{GS}=10V$	-	16.1	-	ns	
t <sub>f</sub>	Turn-off Fall Time	VGS-10V	-	2.3	-	ns	
Drain-Soul	rce Diode Characteristics and Maxim	um Ratings					
	Maximum Continuous Drain to Source Diode Forward				_		
Is	Current		-	-	5	Α	
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	30	Α	
V <sub>SD</sub>	Drain to Source Diode Forward	V <sub>GS</sub> =0V, I <sub>S</sub> =15A	_	_	1.2	V	
	Voltage	V G5-0 V, 15-10A		_	1.4	V	
trr	Body Diode Reverse Recovery Time	  -   T <sub>J</sub> =25℃,I <sub>F</sub> =15A,	-	35	-	ns	
Qrr	Body Diode Reverse Recovery	dl/dt=100A/µs	_	53	-	nC	
	Charge						

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

<sup>2.</sup> EAS condition : TJ=25  $^{\circ}\text{C}$  ,VDD=30V,VG=10V,L=0.5mH,Rg=25 $\Omega$ ,IAS=6.1A

<sup>3.</sup> Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



## **Typical Performance Characteristics**

Figure1: Output Characteristics

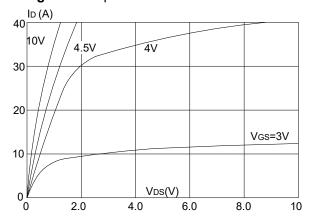


Figure 3:On-resistance vs. Drain Current

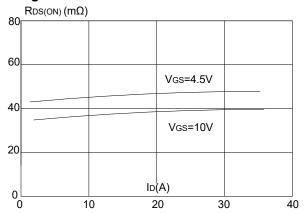


Figure 5: Gate Charge Characteristics

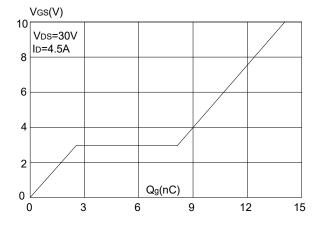


Figure 2: Typical Transfer Characteristics

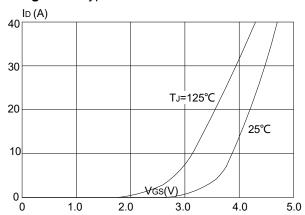


Figure 4: Body Diode Characteristics

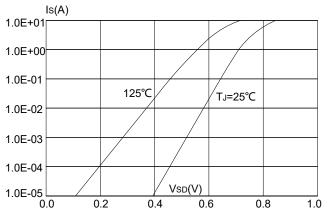
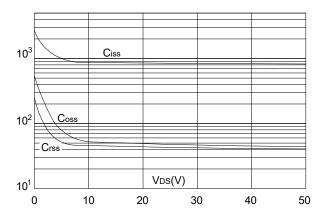


Figure 6: Capacitance Characteristics





**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature

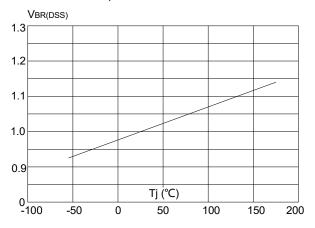
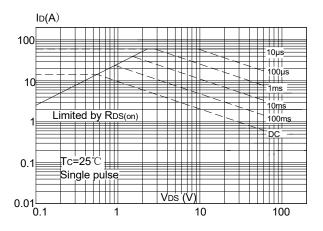
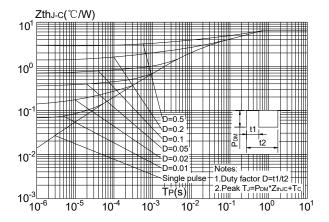
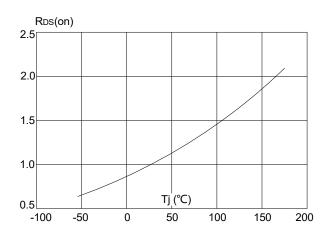


Figure 9: Maximum Safe Operating Area

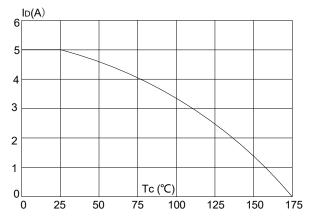


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case

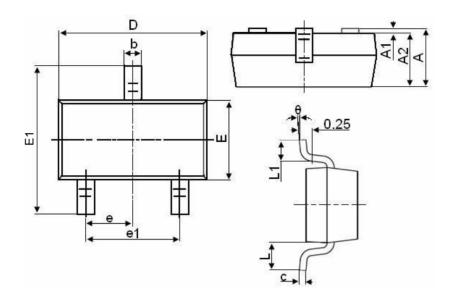




**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



### **SOT-23-3L Package Information**



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
Е	1.500	1.700	
E1	2.650	2.950	
е	0.950TYP		
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	

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